

Michael J Manfra

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178
ext. papers

5,756
ext. citations

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L-index

#	Paper	IF	Citations
167	Direct imaging of reverse-bias leakage through pure screw dislocations in GaN films grown by molecular beam epitaxy on GaN templates. <i>Applied Physics Letters</i> , 2002 , 81, 79-81	3.4	247
166	Inhomogeneous spatial distribution of reverse bias leakage in GaN Schottky diodes. <i>Applied Physics Letters</i> , 2001 , 78, 1685-1687	3.4	246
165	Scaling of Majorana Zero-Bias Conductance Peaks. <i>Physical Review Letters</i> , 2017 , 119, 136803	7.4	221
164	Poole-Frenkel electron emission from the traps in AlGaIn/GaN transistors. <i>Journal of Applied Physics</i> , 2004 , 95, 6414-6419	2.5	149
163	Noise Suppression Using Symmetric Exchange Gates in Spin Qubits. <i>Physical Review Letters</i> , 2016 , 116, 116801	7.4	145
162	Evidence of topological superconductivity in planar Josephson junctions. <i>Nature</i> , 2019 , 569, 89-92	50.4	121
161	High-fidelity entangling gate for double-quantum-dot spin qubits. <i>Npj Quantum Information</i> , 2017 , 3,	8.6	120
160	Collective non-perturbative coupling of 2D electrons with high-quality-factor terahertz cavity photons. <i>Nature Physics</i> , 2016 , 12, 1005-1011	16.2	110
159	Effect of growth stoichiometry on the electrical activity of screw dislocations in GaN films grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2001 , 78, 3980-3982	3.4	104
158	Nonconventional odd-denominator fractional quantum Hall states in the second Landau level. <i>Physical Review Letters</i> , 2010 , 105, 246808	7.4	90
157	High-mobility AlGaIn/GaN heterostructures grown by molecular-beam epitaxy on GaN templates prepared by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , 2000 , 77, 2888-2890	3.4	84
156	Mechanisms of gate lag in GaN/AlGaIn/GaN high electron mobility transistors. <i>Superlattices and Microstructures</i> , 2003 , 34, 33-53	2.8	83
155	Molecular Beam Epitaxy of Ultra-High-Quality AlGaAs/GaAs Heterostructures: Enabling Physics in Low-Dimensional Electronic Systems. <i>Annual Review of Condensed Matter Physics</i> , 2014 , 5, 347-373	19.7	81
154	Induced superconductivity in high-mobility two-dimensional electron gas in gallium arsenide heterostructures. <i>Nature Communications</i> , 2015 , 6, 7426	17.4	71
153	Superconducting gatemon qubit based on a proximitized two-dimensional electron gas. <i>Nature Nanotechnology</i> , 2018 , 13, 915-919	28.7	68
152	Superradiant decay of cyclotron resonance of two-dimensional electron gases. <i>Physical Review Letters</i> , 2014 , 113, 047601	7.4	68
151	Electric and Magnetic Tuning Between the Trivial and Topological Phases in InAs/GaSb Double Quantum Wells. <i>Physical Review Letters</i> , 2015 , 115, 036803	7.4	66

150	High mobility AlGa _N /Ga _N heterostructures grown by plasma-assisted molecular beam epitaxy on semi-insulating Ga _N templates prepared by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2002 , 92, 338-345	2.5	66
149	Direct observation of anyonic braiding statistics. <i>Nature Physics</i> , 2020 , 16, 931-936	16.2	61
148	Observation of a transition from a topologically ordered to a spontaneously broken symmetry phase. <i>Nature Physics</i> , 2016 , 12, 191-195	16.2	56
147	Notch filtering the nuclear environment of a spin qubit. <i>Nature Nanotechnology</i> , 2017 , 12, 16-20	28.7	55
146	Repeatable low-temperature negative-differential resistance from Al _{0.18} Ga _{0.82} N/GaN resonant tunneling diodes grown by molecular-beam epitaxy on free-standing Ga _N substrates. <i>Applied Physics Letters</i> , 2012 , 100, 252105	3.4	54
145	Transport and percolation in a low-density high-mobility two-dimensional hole system. <i>Physical Review Letters</i> , 2007 , 99, 236402	7.4	54
144	Vacuum Bloch- Siegert shift in Landau polaritons with ultra-high cooperativity. <i>Nature Photonics</i> , 2018 , 12, 324-329	33.9	52
143	Electron mobility exceeding 160000cm ² /Vs in AlGa _N /Ga _N heterostructures grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2004 , 85, 5394-5396	3.4	51
142	Dynamics of trapped charge in Ga _N /AlGa _N /Ga _N high electron mobility transistors grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2004 , 84, 422-424	3.4	47
141	Impact of Si doping on radio frequency dispersion in unpassivated Ga _N /AlGa _N /Ga _N high-electron-mobility transistors grown by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2003 , 82, 4361-4363	3.4	45
140	Effect of strain on stripe phases in the quantum Hall regime. <i>Physical Review Letters</i> , 2011 , 106, 016804	7.4	43
139	Electron mobility in very low density Ga _N /AlGa _N /Ga _N heterostructures. <i>Applied Physics Letters</i> , 2004 , 85, 1722-1724	3.4	41
138	Aharonov-Bohm interference of fractional quantum Hall edge modes. <i>Nature Physics</i> , 2019 , 15, 563-569	16.2	40
137	Modified MBE hardware and techniques and role of gallium purity for attainment of two dimensional electron gas mobility >35006 cm ² /V s in AlGaAs/GaAs quantum wells grown by MBE. <i>Journal of Crystal Growth</i> , 2016 , 441, 71-77	1.6	40
136	Acoustic phonon scattering in a low density, high mobility AlGa _N /Ga _N field-effect transistor. <i>Applied Physics Letters</i> , 2005 , 86, 252108	3.4	40
135	Electron scattering in AlGa _N /Ga _N structures. <i>Applied Physics Letters</i> , 2004 , 84, 1507-1509	3.4	40
134	Spectrum of the Nuclear Environment for GaAs Spin Qubits. <i>Physical Review Letters</i> , 2017 , 118, 177702	7.4	40
133	Coherent spin-state transfer via Heisenberg exchange. <i>Nature</i> , 2019 , 573, 553-557	50.4	39

132	High mobility two-dimensional hole system in GaAs/AlGaAs quantum wells grown on (100) GaAs substrates. <i>Applied Physics Letters</i> , 2005 , 86, 162106	3-4	39
131	Full control of quadruple quantum dot circuit charge states in the single electron regime. <i>Applied Physics Letters</i> , 2014 , 104, 183111	3-4	35
130	Quantitative analysis of the disorder broadening and the intrinsic gap for the $\nu=5/2$ fractional quantum Hall state. <i>Physical Review B</i> , 2011 , 84,	3-3	35
129	Dislocation and morphology control during molecular-beam epitaxy of AlGaIn/GaN heterostructures directly on sapphire substrates. <i>Applied Physics Letters</i> , 2002 , 81, 1456-1458	3-4	34
128	Contrasting energy scales of reentrant integer quantum Hall states. <i>Physical Review B</i> , 2012 , 86,	3-3	33
127	High-reflectivity ultraviolet AlGaIn/AlGaIn distributed Bragg reflectors. <i>Applied Physics Letters</i> , 2006 , 88, 171101	3-4	32
126	Nonparabolicity of the conduction band of wurtzite GaN. <i>Applied Physics Letters</i> , 2003 , 83, 4553-4555	3-4	32
125	Quantized Conductance and Large g-Factor Anisotropy in InSb Quantum Point Contacts. <i>Nano Letters</i> , 2016 , 16, 7509-7513	11.5	31
124	Observation of Dirac bands in artificial graphene in small-period nanopatterned GaAs quantum wells. <i>Nature Nanotechnology</i> , 2018 , 13, 29-33	28.7	31
123	Topological superconductivity in hybrid devices. <i>Nature Physics</i> , 2020 , 16, 718-724	16.2	30
122	Decoupling Edge Versus Bulk Conductance in the Trivial Regime of an InAs/GaSb Double Quantum Well Using Corbino Ring Geometry. <i>Physical Review Letters</i> , 2016 , 117, 077701	7-4	30
121	Evidence for effective mass reduction in GaAs/AlGaAs quantum wells. <i>Physical Review B</i> , 2013 , 87,	3-3	30
120	Near-infrared intersubband absorption in molecular-beam epitaxy-grown lattice-matched InAlN/GaN superlattices. <i>Applied Physics Letters</i> , 2009 , 94, 161111	3-4	29
119	A cryogenic CMOS chip for generating control signals for multiple qubits. <i>Nature Electronics</i> , 2021 , 4, 64-70	28.4	29
118	$\nu=5/2$ fractional quantum Hall state in the presence of alloy disorder. <i>Physical Review Letters</i> , 2014 , 112, 116804	7-4	28
117	Improvement of near-infrared absorption linewidth in AlGaIn/GaN superlattices by optimization of delta-doping location. <i>Applied Physics Letters</i> , 2012 , 101, 102104	3-4	28
116	Quantum and transport lifetimes in a tunable low-density AlGaIn/GaN two-dimensional electron gas. <i>Applied Physics Letters</i> , 2004 , 85, 5278-5280	3-4	26
115	Fast spin exchange across a multielectron mediator. <i>Nature Communications</i> , 2019 , 10, 1196	17.4	25

114	Direct entropy measurement in a mesoscopic quantum system. <i>Nature Physics</i> , 2018 , 14, 1083-1086	16.2	25
113	Comparative study of intersubband absorption in AlGaN/GaN and AlInN/GaN superlattices: Impact of material inhomogeneities. <i>Physical Review B</i> , 2013 , 88,	3.3	25
112	Gate-tunable high mobility remote-doped InSb/In _{1-x} Al _x Sb quantum well heterostructures. <i>Applied Physics Letters</i> , 2015 , 106, 142103	3.4	24
111	III-V gate-all-around nanowire MOSFET process technology: From 3D to 4D 2012 ,		24
110	Giant Spin-Orbit Splitting in Inverted InAs/GaSb Double Quantum Wells. <i>Physical Review Letters</i> , 2017 , 118, 016801	7.4	23
109	Spin-orbit interaction in a dual gated InAs/GaSb quantum well. <i>Physical Review B</i> , 2017 , 96,	3.3	23
108	Impact of spin-orbit coupling on quantum Hall nematic phases. <i>Physical Review Letters</i> , 2007 , 98, 206804	7.4	22
107	Surface topography and chemistry shape cellular behavior on wide band-gap semiconductors. <i>Acta Biomaterialia</i> , 2014 , 10, 2455-62	10.8	21
106	Symmetric operation of the resonant exchange qubit. <i>Physical Review B</i> , 2017 , 96,	3.3	21
105	Effects of forming gas anneal on ultrathin InGaAs nanowire metal-oxide-semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2013 , 102, 093505	3.4	21
104	Reorientation of quantum Hall stripes within a partially filled Landau level. <i>Physical Review B</i> , 2016 , 93,	3.3	20
103	h/e Superconducting Quantum Interference through Trivial Edge States in InAs. <i>Physical Review Letters</i> , 2018 , 120, 047702	7.4	19
102	Homogeneous AlGaIn/GaN superlattices grown on free-standing (11 $\bar{1}$ 00) GaN substrates by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 103, 232103	3.4	19
101	Coherent vertical electron transport and interface roughness effects in AlGaIn/GaN intersubband devices. <i>Journal of Applied Physics</i> , 2015 , 118, 224308	2.5	19
100	Quasi-ballistic thermal transport in Al _{0.1} Ga _{0.9} N thin film semiconductors. <i>Applied Physics Letters</i> , 2016 , 109, 243107	3.4	18
99	Ballistic superconductivity and tunable μ junctions in InSb quantum wells. <i>Nature Communications</i> , 2019 , 10, 3764	17.4	17
98	Possible nematic to smectic phase transition in a two-dimensional electron gas at half-filling. <i>Nature Communications</i> , 2017 , 8, 1536	17.4	17
97	Near-Infrared Absorption in Lattice-Matched AlInN/GaN and Strained AlGaIn/GaN Heterostructures Grown by MBE on Low-Defect GaN Substrates. <i>Journal of Electronic Materials</i> , 2012 , 41, 881-886	1.9	17

96	Readout of singlet-triplet qubits at large magnetic field gradients. <i>Physical Review B</i> , 2018 , 98,	3.3	17
95	Evidence for a new symmetry breaking mechanism reorienting quantum Hall nematics. <i>Physical Review B</i> , 2016 , 93,	3.3	16
94	200nm Channel length InGaAs gate-all-around nanowire MOSFETs with EOT=1.2nm and lowest SS=63mV/dec 2012 ,		16
93	Microwave-induced resistance oscillations in a back-gated GaAs quantum well. <i>Physical Review B</i> , 2017 , 95,	3.3	15
92	Coherent transport through a Majorana island in an Aharonov-Bohm interferometer. <i>Nature Communications</i> , 2020 , 11, 3212	17.4	15
91	Electron-electron interactions and the paired-to-nematic quantum phase transition in the second Landau level. <i>Nature Communications</i> , 2018 , 9, 2400	17.4	15
90	Low-temperature illumination and annealing of ultrahigh quality quantum wells. <i>Physical Review B</i> , 2014 , 90,	3.3	15
89	Quantum transport in high mobility AlGaIn/GaN 2DEGs and nanostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1706-1712	1.3	15
88	Surface morphology and electronic properties of dislocations in AlGaIn/GaN heterostructures. <i>Journal of Electronic Materials</i> , 2001 , 30, 110-114	1.9	15
87	Hybridization of Subgap States in One-Dimensional Superconductor-Semiconductor Coulomb Islands. <i>Physical Review Letters</i> , 2018 , 121, 256803	7.4	15
86	Quantum lifetime in ultrahigh quality GaAs quantum wells: Relationship to $\hbar/2$ and impact of density fluctuations. <i>Physical Review B</i> , 2017 , 96,	3.3	14
85	Negative Spin Exchange in a Multielectron Quantum Dot. <i>Physical Review Letters</i> , 2017 , 119, 227701	7.4	14
84	Onset of quantum criticality in the topological-to-nematic transition in a two-dimensional electron gas at filling factor $\nu=5/2$. <i>Physical Review B</i> , 2017 , 96,	3.3	14
83	High-mobility InAs 2DEGs on GaSb substrates: A platform for mesoscopic quantum transport. <i>Physical Review Materials</i> , 2018 , 2,	3.2	14
82	Spin of a Multielectron Quantum Dot and Its Interaction with a Neighboring Electron. <i>Physical Review X</i> , 2018 , 8,	9.1	13
81	Emerging many-body effects in semiconductor artificial graphene with low disorder. <i>Nature Communications</i> , 2018 , 9, 3299	17.4	13
80	In-surface confinement of topological insulator nanowire surface states. <i>Applied Physics Letters</i> , 2015 , 107, 121605	3.4	13
79	Cyclotron mass of two-dimensional holes in (100) oriented GaAs/AlGaAs heterostructures. <i>Applied Physics Letters</i> , 2008 , 92, 012109	3.4	13

78	Magnetoplasmon resonance in a two-dimensional electron system driven into a zero-resistance state. <i>Physical Review B</i> , 2012 , 85,	3-3	12
77	Exploration of the limits to mobility in two-dimensional hole systems in GaAs/AlGaAs quantum wells. <i>Physical Review B</i> , 2012 , 85,	3-3	12
76	Mobility in excess of 106 cm ² /V s in InAs quantum wells grown on lattice mismatched InP substrates. <i>Applied Physics Letters</i> , 2017 , 111, 142106	3-4	12
75	Conditional teleportation of quantum-dot spin states. <i>Nature Communications</i> , 2020 , 11, 3022	17.4	11
74	Optical Emission Spectroscopy Study of Competing Phases of Electrons in the Second Landau Level. <i>Physical Review Letters</i> , 2016 , 116, 016801	7-4	11
73	Shubnikov-de Haas oscillations in a two-dimensional electron gas under subterahertz radiation. <i>Physical Review B</i> , 2015 , 92,	3-3	11
72	Growth and electrical characterization of Al _{0.24} Ga _{0.76} As/Al _x Ga _{1-x} As/Al _{0.24} Ga _{0.76} As modulation-doped quantum wells with extremely low x. <i>Applied Physics Letters</i> , 2013 , 102, 252103	3-4	11
71	Supercurrent rectification and magnetochiral effects in symmetric Josephson junctions. <i>Nature Nanotechnology</i> , 2021 ,	28.7	11
70	Kinetic instability of AlGaIn alloys during MBE growth under metal-rich conditions on m-plane GaN miscut towards the -c axis. <i>Journal of Applied Physics</i> , 2018 , 123, 161581	2-5	10
69	Effect of density on quantum Hall stripe orientation in tilted magnetic fields. <i>Physical Review B</i> , 2017 , 95,	3-3	9
68	Transport of a sliding Wigner crystal in the four flux composite fermion regime. <i>Physical Review B</i> , 2015 , 92,	3-3	9
67	Magnetotransport in Zener tunneling regime in a high-mobility two-dimensional hole gas. <i>Physical Review B</i> , 2009 , 80,	3-3	9
66	Scattering mechanisms in a high-mobility low-density carbon-doped (100) GaAs two-dimensional hole system. <i>Physical Review B</i> , 2011 , 83,	3-3	9
65	Impact of growth conditions and strain on indium incorporation in non-polar m-plane (101̄0) InGaIn grown by plasma-assisted molecular beam epitaxy. <i>APL Materials</i> , 2019 , 7, 121109	5-7	9
64	Coherent Multispin Exchange Coupling in a Quantum-Dot Spin Chain. <i>Physical Review X</i> , 2020 , 10,	9-1	8
63	Effect of dislocations on local transconductance in AlGaIn/GaN heterostructures as imaged by scanning gate microscopy. <i>Applied Physics Letters</i> , 2003 , 83, 4559-4561	3-4	8
62	Adiabatic quantum state transfer in a semiconductor quantum-dot spin chain. <i>Nature Communications</i> , 2021 , 12, 2156	17.4	8
61	Gate-defined quantum point contact in an InAs two-dimensional electron gas. <i>Physical Review B</i> , 2019 , 100,	3-3	7

60	Relating Andreev Bound States and Supercurrents in Hybrid Josephson Junctions. <i>Physical Review Letters</i> , 2020 , 124, 226801	7.4	7
59	Optimization of edge state velocity in the integer quantum Hall regime. <i>Physical Review B</i> , 2018 , 97,	3.3	7
58	Stability of High-Density Two-Dimensional Excitons against a Mott Transition in High Magnetic Fields Probed by Coherent Terahertz Spectroscopy. <i>Physical Review Letters</i> , 2016 , 117, 207402	7.4	7
57	Topological kink plasmons on magnetic-domain boundaries. <i>Nature Communications</i> , 2019 , 10, 4565	17.4	7
56	Multiphoton processes at cyclotron resonance subharmonics in a two-dimensional electron system under dc and microwave excitation. <i>Physical Review B</i> , 2014 , 90,	3.3	7
55	Particle-hole asymmetry of fractional quantum Hall states in the second Landau level of a two-dimensional hole system. <i>Physical Review B</i> , 2011 , 83,	3.3	7
54	Floquet-enhanced spin swaps. <i>Nature Communications</i> , 2021 , 12, 2142	17.4	7
53	Dramatic enhancement of near-infrared intersubband absorption in c-plane AlInN/GaN superlattices. <i>Applied Physics Letters</i> , 2016 , 108, 121108	3.4	7
52	Observation of electron states of small period artificial graphene in nano-patterned GaAs quantum wells. <i>Applied Physics Letters</i> , 2016 , 109, 113101	3.4	7
51	Intersubband Transitions in Nonpolar m-Plane AlGaIn/GaN Heterostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700828	1.6	7
50	Apparent temperature-induced reorientation of quantum Hall stripes. <i>Physical Review B</i> , 2017 , 95,	3.3	6
49	Photoluminescence study of non-polar m-plane InGaIn and nearly strain-balanced InGaIn/AlGaIn superlattices. <i>Journal of Applied Physics</i> , 2020 , 127, 185702	2.5	6
48	Gapped excitations of unconventional fractional quantum Hall effect states in the second Landau level. <i>Physical Review B</i> , 2015 , 92,	3.3	6
47	Mesoscopic structures and two-dimensional hole systems in fully field effect controlled heterostructures. <i>Applied Physics Letters</i> , 2007 , 91, 033510	3.4	6
46	Band Structure Extraction at Hybrid Narrow-Gap Semiconductor-Metal Interfaces. <i>Advanced Science</i> , 2021 , 8, 2003087	13.6	6
45	Electron-Hole Asymmetric Chiral Breakdown of Reentrant Quantum Hall States. <i>Physical Review Letters</i> , 2016 , 117, 166805	7.4	6
44	Hydrodynamic and Ballistic Transport over Large Length Scales in GaAs/AlGaAs. <i>Physical Review Letters</i> , 2021 , 126, 076803	7.4	6
43	Electron bubbles and the structure of the orbital wave function. <i>Physical Review B</i> , 2019 , 99,	3.3	5

42	Observation of new plasmons in the fractional quantum Hall effect: Interplay of topological and nematic orders. <i>Science Advances</i> , 2019 , 5, eaav3407	14.3	5
41	Quantum Dots in an InSb Two-Dimensional Electron Gas. <i>Physical Review Applied</i> , 2020 , 13,	4.3	5
40	Field-effect-induced two-dimensional electron gas utilizing modulation-doped ohmic contacts. <i>Solid State Communications</i> , 2014 , 197, 20-24	1.6	5
39	Repairing the surface of InAs-based topological heterostructures. <i>Journal of Applied Physics</i> , 2020 , 128, 114301	2.5	5
38	Indium surfactant assisted epitaxy of non-polar (1010) AlGaIn/InGaIn multiple quantum well heterostructures. <i>Journal of Applied Physics</i> , 2020 , 128, 115701	2.5	5
37	Josephson Inductance as a Probe for Highly Ballistic Semiconductor-Superconductor Weak Links. <i>Physical Review Letters</i> , 2021 , 126, 037001	7.4	5
36	Long-Distance Superexchange between Semiconductor Quantum-Dot Electron Spins. <i>Physical Review Letters</i> , 2021 , 126, 017701	7.4	5
35	High-temperature resistivity measured at $\nu=5/2$ as a predictor of the two-dimensional electron gas quality in the $N=1$ Landau level. <i>Physical Review B</i> , 2017 , 95,	3.3	4
34	Anomalous Nematic States in High Half-Filled Landau Levels. <i>Physical Review Letters</i> , 2020 , 124, 067601	7.4	4
33	Resistively detected high-order magnetoplasmons in a high-quality two-dimensional electron gas. <i>Physical Review B</i> , 2016 , 93,	3.3	4
32	Free standing GaN nano membrane by laser lift-off method. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1432, 53		4
31	High power GaN/AlGaIn/GaN HEMTs operating at 2 to 25 GHz grown by plasma-assisted MBE. <i>Physica Status Solidi A</i> , 2003 , 200, 175-178		4
30	Toward durable Al-InSb hybrid heterostructures via epitaxy of 2ML interfacial InAs screening layers. <i>Physical Review Materials</i> , 2019 , 3,	3.2	4
29	Resistivity anisotropy of quantum Hall stripe phases. <i>Physical Review B</i> , 2019 , 100,	3.3	4
28	Effect of illumination on quantum lifetime in GaAs quantum wells. <i>Physical Review B</i> , 2018 , 98,	3.3	4
27	Integrated high electron mobility transistors in GaAs/AlGaAs heterostructures for amplification at sub-Kelvin temperatures. <i>Applied Physics Letters</i> , 2019 , 114, 053104	3.4	3
26	Millimeter wave transmission spectroscopy of gated two-dimensional hole systems. <i>Applied Physics Letters</i> , 2012 , 100, 192104	3.4	3
25	Effect of Rashba and Dresselhaus spin-orbit coupling on supercurrent rectification and magnetochiral anisotropy of ballistic Josephson junctions. <i>Journal of Physics Condensed Matter</i> , 2022 ,	1.8	3

24	InSbAs Two-Dimensional Electron Gases as a Platform for Topological Superconductivity. <i>Nano Letters</i> , 2021 , 21, 9990-9996	11.5	3
23	Simultaneous Operations in a Two-Dimensional Array of Singlet-Triplet Qubits. <i>PRX Quantum</i> , 2021 , 2,	6.1	3
22	Reduction of charge noise in shallow GaAs/AlGaAs heterostructures with insulated gates. <i>Applied Physics Letters</i> , 2020 , 117, 133504	3.4	3
21	LARGE CYCLOTRON-RESONANCE LINE SPLITTING OF TWO-DIMENSIONAL ELECTRONS IN AlGa _N /Ga _N AND AlGaAs/GaAs HETEROSTRUCTURES. <i>International Journal of Modern Physics B</i> , 2004 , 18, 3761-3768	1.1	2
20	Anodic oxidation of epitaxial superconductor-semiconductor hybrids. <i>Physical Review Materials</i> , 2021 , 5,	3.2	2
19	Mid-infrared intersubband absorption in strain-balanced non-polar (In)AlGa _N /InGa _N multi-quantum wells. <i>Optical Materials Express</i> , 2021 , 11, 3284	2.6	2
18	Impact of short-range scattering on the metallic transport of strongly correlated two-dimensional holes in GaAs quantum wells. <i>Physical Review B</i> , 2014 , 90,	3.3	1
17	Strong heavy-to-light hole intersubband absorption in the valence band of carbon-doped GaAs/AlAs superlattices. <i>Journal of Applied Physics</i> , 2013 , 113, 053103	2.5	1
16	Josephson junctions via anodization of epitaxial Al on an InAs heterostructure. <i>Applied Physics Letters</i> , 2021 , 119, 172601	3.4	1
15	Observation of Photoinduced Terahertz Gain in GaAs Quantum Wells: Evidence for Radiative Two-Exciton-to-Biexciton Scattering. <i>Physical Review Letters</i> , 2020 , 125, 167401	7.4	1
14	Observation of Flat Bands in Gated Semiconductor Artificial Graphene. <i>Physical Review Letters</i> , 2021 , 126, 106402	7.4	1
13	Effect of density on microwave-induced resistance oscillations in back-gated GaAs quantum wells. <i>Physical Review B</i> , 2018 , 98,	3.3	1
12	Domain Textures in the Fractional Quantum Hall Effect.. <i>Physical Review Letters</i> , 2022 , 128, 017401	7.4	0
11	Impact of bulk-edge coupling on observation of anyonic braiding statistics in quantum Hall interferometers.. <i>Nature Communications</i> , 2022 , 13, 344	17.4	0
10	Accurate characterization of tip-induced potential using electron interferometry. <i>Applied Physics Letters</i> , 2020 , 117, 193101	3.4	0
9	Hidden Quantum Hall Stripes in Al _x Ga _{1-x} As/Al _{0.24} Ga _{0.76} As Quantum Wells. <i>Physical Review Letters</i> , 2020 , 125, 236803	7.4	0
8	Precision measurement of electron-electron scattering in GaAs/AlGaAs using transverse magnetic focusing. <i>Nature Communications</i> , 2021 , 12, 5048	17.4	0
7	Overcoming anomalous suppression of m-plane AlGa _N growth by molecular-beam epitaxy using indium as a surfactant. <i>Journal of Applied Physics</i> , 2021 , 130, 105702	2.5	0

6	Measurements of cyclotron resonance of the interfacial states in strong spin-orbit coupled 2D electron gases proximitized with aluminum. <i>Applied Physics Letters</i> , 2022 , 120, 142105	3.4	0
5	The dependence of aluminum lattice orientation on semiconductor lattice parameter in planar InAs/Al hybrid heterostructures. <i>Journal of Crystal Growth</i> , 2020 , 535, 125570	1.6	
4	The Effect of the Ion Beam Energy on M-plane InGaN Layer Preparation for STEM. <i>Microscopy and Microanalysis</i> , 2019 , 25, 1702-1703	0.5	
3	Heavy-to-light hole intersubband absorption in the valence band of GaAs/AlAs heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1509, 1		
2	A capacitance spectroscopy-based platform for realizing gate-defined electronic lattices. <i>Journal of Applied Physics</i> , 2018 , 124, 124305	2.5	
1	Photoluminescence Study of Carrier Localization and Recombination in Nearly Strain-Balanced Nonpolar InGaN/AlGaN Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , 2100569	1.3	